

# SPECIFICATION

Device Name : IGBT MODULE

Type Name : 2MBI100U4A-120

Spec. No. : MS5F 6061

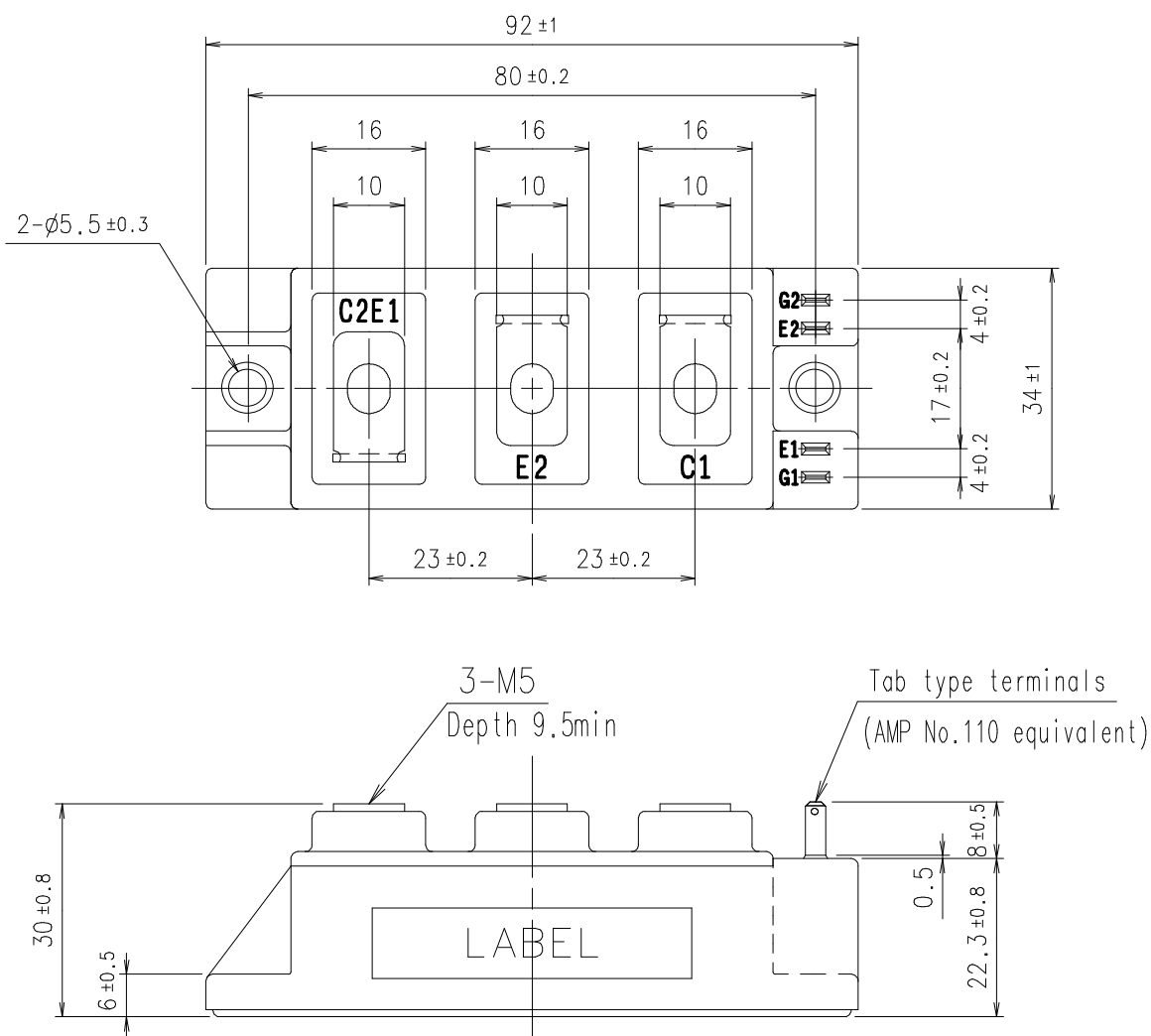
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	DATE	NAME	APPROVED	<b>Fuji Electric Device Technology Co.,Ltd.</b>		
DRAWN	Mar.- 09 -'05	S.Miyashita	Y.Seki	DWG.NO.	MS5F6061	1 /
CHECKED	Mar.- 09 -'05	T.Miyasaka				13
CHECKED	- -	K.Yamada				



2MBI100U4A-120

1. Outline Drawing ( Unit : mm )



2. Equivalent circuit



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### 3. Absolute Maximum Ratings ( at Tc= 25°C unless otherwise specified )

Items		Symbols	Conditions	Maximum Ratings	Units	
Collector-Emitter voltage		V <sub>CES</sub>		1200	V	
Gate-Emitter voltage		V <sub>GES</sub>		±20	V	
Collector current	I <sub>c</sub>		Continuous	T <sub>c</sub> =25°C	150	A
			T <sub>c</sub> =80°C	100		
	I <sub>cp</sub>	1ms	T <sub>c</sub> =25°C	300		
			T <sub>c</sub> =80°C	200		
	-I <sub>c</sub>			100		
-I <sub>c</sub> pulse	1ms		200			
Collector Power Dissipation		P <sub>c</sub>	1 device	540	W	
Junction temperature		T <sub>j</sub>		+150	°C	
Storage temperature		T <sub>stg</sub>		-40 to +125		
Isolation voltage	between terminal and copper base (*1)	V <sub>iso</sub>	AC : 1min.	2500	VAC	
Screw Torque	Mounting (*2)	-		3.5	N m	
	Terminals (*2)	-				

(\*1) All terminals should be connected together when isolation test will be done.

(\*2) Recommendable Value : 2.5 to 3.5 Nm (M5)

### 4. Electrical characteristics ( at Tj= 25°C unless otherwise specified )

Items	Symbols	Conditions	Characteristics			Units	
			min.	typ.	max.		
Zero gate voltage collector current	I <sub>CES</sub>	V <sub>CE</sub> =1200V V <sub>GE</sub> =0V	-	-	1.0	mA	
Gate-Emitter leakage current	I <sub>GES</sub>	V <sub>CE</sub> =0V V <sub>GE</sub> =±20V	-	-	200	nA	
Gate-Emitter threshold voltage	V <sub>GE(th)</sub>	V <sub>CE</sub> =20V I <sub>c</sub> =100mA	4.5	6.5	8.5	V	
Collector-Emitter saturation voltage	V <sub>CE(sat)</sub> (terminal)	I <sub>c</sub> =100A V <sub>GE</sub> =15V	T <sub>j</sub> =25°C	-	2.05	2.20	V
			T <sub>j</sub> =125°C	-	2.25	-	
	V <sub>CE(sat)</sub> (chip)		T <sub>j</sub> =25°C	-	1.90	2.05	
			T <sub>j</sub> =125°C	-	2.10	-	
Input capacitance	C <sub>ies</sub>	V <sub>CE</sub> =10V, V <sub>GE</sub> =0V, f=1MHz	-	11	-	nF	
Turn-on time	t <sub>on</sub>	V <sub>cc</sub> =600V	-	0.32	1.20	us	
	t <sub>r</sub>	I <sub>c</sub> =100A	-	0.10	0.60		
	t <sub>r(i)</sub>	V <sub>GE</sub> =±15V	-	0.03	-		
Turn-off time	t <sub>off</sub>	R <sub>G</sub> =5.6Ω	-	0.41	1.00	us	
	t <sub>f</sub>		-	0.07	0.30		
Forward on voltage	V <sub>F</sub> (terminal)	I <sub>F</sub> =100A V <sub>GE</sub> =0V	T <sub>j</sub> =25°C	-	1.80	1.95	V
			T <sub>j</sub> =125°C	-	1.90	-	
	V <sub>F</sub> (chip)		T <sub>j</sub> =25°C	-	1.65	1.80	
			T <sub>j</sub> =125°C	-	1.75	-	
Reverse recovery time	t <sub>rr</sub>	I <sub>F</sub> =100A	-	-	0.35	us	
Lead resistance, terminal-chip (*3)	R <sub>lead</sub>		-	1.39	-	mΩ	

(\*3) Biggest internal terminal resistance among arm.

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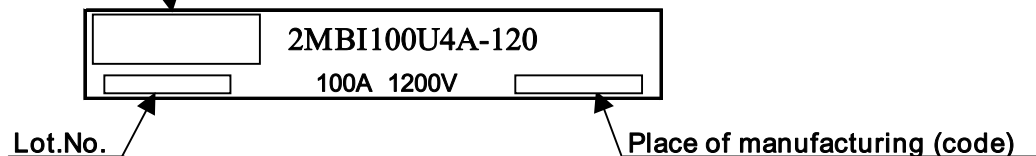
### 5. Thermal resistance characteristics

Items	Symbols	Conditions	Characteristics			Units
			min.	typ.	max.	
Thermal resistance(1 device)	Rth(j-c)	IGBT	-	-	0.23	°C/W
		FWD	-	-	0.40	
Contact Thermal resistance (1 device) (*4)	Rth(c-f)	with Thermal Compound	-	0.05	-	

(\*4) This is the value which is defined mounting on the additional cooling fin with thermal compound.

### 6. Indication on module

#### Logo of production



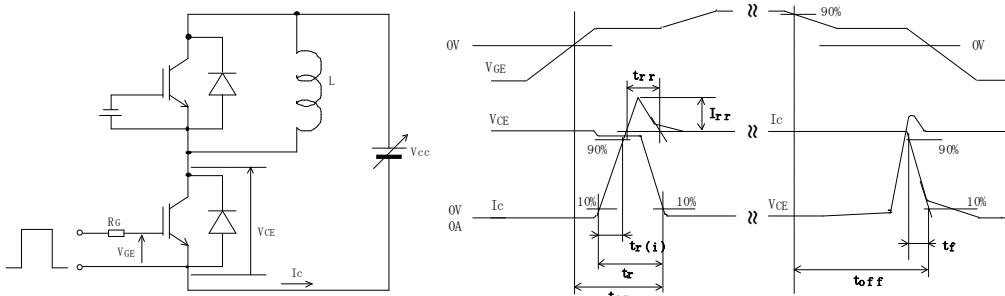
### 7. Applicable category

This specification is applied to IGBT-Module named 2MBI100U4A-120.

### 8. Storage and transportation notes

- The module should be stored at a standard temperature of 5 to 35°C and humidity of 45 to 75% .
- Store modules in a place with few temperature changes in order to avoid condensation on the module surface.
- Avoid exposure to corrosive gases and dust.
- Avoid excessive external force on the module.
- Store modules with unprocessed terminals.
- Do not drop or otherwise shock the modules when transporting.

### 9. Definitions of switching time



### 10. Packing and Labeling

Display on the packing box

- Logo of production
- Type name
- Lot No
- Products quantity in a packing box

11. Reliability test results

**Reliability Test Items**

Test categories	Test items	Test methods and conditions	Reference norms EIAJ ED-4701 (Aug.-2001 edition)	Number of sample	Acceptance number
Mechanical Tests	1 Terminal Strength (Pull test)	Pull force : 40N Test time : 10±1 sec.	Test Method 401 Method I	5	(0 : 1)
	2 Mounting Strength	Screw torque : 2.5 ~ 3.5 N·m (M5) Test time : 10±1 sec.	Test Method 402 method II	5	(0 : 1)
	3 Vibration	Range of frequency : 10 ~ 500Hz Sweeping time : 15 min. Acceleration : 100m/s <sup>2</sup> Sweeping direction : Each X,Y,Z axis Test time : 6 hr. (2hr./direction)	Test Method 403 Reference 1 Condition code B	5	(0 : 1)
	4 Shock	Maximum acceleration : 5000m/s <sup>2</sup> Pulse width : 1.0msec. Direction : Each X,Y,Z axis Test time : 3 times/direction	Test Method 404 Condition code B	5	(0 : 1)
Environment Tests	1 High Temperature Storage	Storage temp. : 125±5 °C Test duration : 1000hr.	Test Method 201	5	(0 : 1)
	2 Low Temperature Storage	Storage temp. : -40±5 °C Test duration : 1000hr.	Test Method 202	5	(0 : 1)
	3 Temperature Humidity Storage	Storage temp. : 85±2 °C Relative humidity : 85±5% Test duration : 1000hr.	Test Method 103 Test code C	5	(0 : 1)
	4 Unsaturated Pressurized Vapor	Test temp. : 120±2 °C Test humidity : 85±5% Test duration : 96hr.	Test Method 103 Test code E	5	(0 : 1)
	5 Temperature Cycle	Test temp. : ┌ Low temp. -40±5 °C ├ High temp. 125 ±5 °C └ RT 5 ~ 35 °C Dwell time : High ~ RT ~ Low ~ RT 1hr. 0.5hr. 1hr. 0.5hr. Number of cycles : 100 cycles	Test Method 105	5	(0 : 1)
	6 Thermal Shock	Test temp. : ┌ High temp. 100 <sup>+0</sup> °C └ Low temp. 0 <sup>-0</sup> °C Used liquid : Water with ice and boiling water Dipping time : 5 min. par each temp. Transfer time : 10 sec. Number of cycles : 10 cycles	Test Method 307 method I Condition code A	5	(0 : 1)

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## Reliability Test Items

Test categories	Test items	Test methods and conditions	Reference norms EIAJ ED-4701 (Aug.-2001 edition)	Number of sample	Acceptance number
Endurance Tests	1 High temperature Reverse Bias	Test temp. : $T_a = 125 \pm 5 \text{ }^\circ\text{C}$ ( $T_j \leq 150 \text{ }^\circ\text{C}$ ) Bias Voltage : $V_C = 0.8 \times V_{CES}$ Bias Method : Applied DC voltage to C-E $V_{GE} = 0V$ Test duration : 1000hr.	Test Method 101	5	(0 : 1)
	2 High temperature Bias (for gate)	Test temp. : $T_a = 125 \pm 5 \text{ }^\circ\text{C}$ ( $T_j \leq 150 \text{ }^\circ\text{C}$ ) Bias Voltage : $V_C = V_{GE} = +20V$ or $-20V$ Bias Method : Applied DC voltage to G-E $V_{CE} = 0V$ Test duration : 1000hr.	Test Method 101	5	(0 : 1)
	3 Temperature Humidity Bias	Test temp. : $85 \pm 2 \text{ }^\circ\text{C}$ Relative humidity : $85 \pm 5\%$ Bias Voltage : $V_C = 0.8 \times V_{CES}$ Bias Method : Applied DC voltage to C-E $V_{GE} = 0V$ Test duration : 1000hr.	Test Method 102 Condition code C	5	(0 : 1)
	4 Intermittent Operating Life (Power cycle) ( for IGBT )	ON time : 2 sec. OFF time : 18 sec. Test temp. : $\Delta T_j = 100 \pm 5 \text{ deg}$ $T_j \leq 150 \text{ }^\circ\text{C}$ , $T_a = 25 \pm 5 \text{ }^\circ\text{C}$ Number of cycles : 15000 cycles	Test Method 106	5	(0 : 1)

## Failure Criteria

Item	Characteristic	Symbol	Failure criteria		Unit	Note	
			Lower limit	Upper limit			
Electrical characteristic	Leakage current	ICES	-	USL×2	mA		
		±IGES	-	USL×2	μA		
	Gate threshold voltage	VGE(th)	LSL×0.8	USL×1.2	mA		
	Saturation voltage	VCE(sat)	-	USL×1.2	V		
	Forward voltage	VF	-	USL×1.2	V		
	Thermal resistance	IGBT	ΔVGE or ΔVCE	-	USL×1.2	mV	
		FWD	ΔVF	-	USL×1.2	mV	
	Isolation voltage	Viso	Broken insulation		-		
Visual inspection	Visual inspection Peeling Plating and the others	-	The visual sample		-		

LSL : Lower specified limit.  
USL : Upper specified limit.

Note Each parameter measurement read-outs shall be made after stabilizing the components at room ambient for 2 hours minimum, 24 hours maximum after removal from the tests. And in case of the wetting tests, for example, moisture resistance tests, each component shall be made wipe or dry completely before the measurement.

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